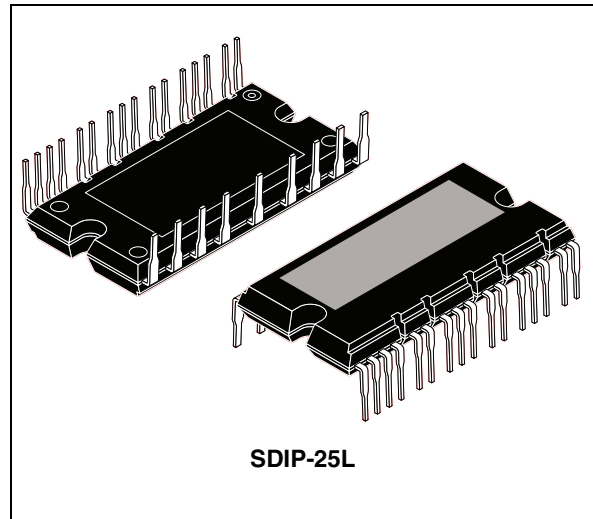


## SLLIMM™ (small low-loss intelligent molded module) IPM, 3-phase inverter - 10 A, 600 V short-circuit rugged IGBT

Datasheet – production data

### Features

- IPM 10 A, 600 V 3-phase IGBT inverter bridge including control ICs for gate driving and free-wheeling diodes
- Short-circuit rugged IGBTs
- $V_{CE(sat)}$  negative temperature coefficient
- 3.3 V, 5 V, 15 V CMOS/TTL inputs comparators with hysteresis and pull down / pull up resistors
- Undervoltage lockout
- Internal bootstrap diode
- Interlocking function
- Shut down function
- DBC substrate leading to low thermal resistance
- Isolation rating of 2500 Vrms/min
- 4.7 kΩ NTC for temperature control
- UL recognized : UL1557 file E81734



home appliances and air conditioners. SLLIMM™ is a trademark of STMicroelectronics.

### Applications

- 3-phase inverters for motor drives
- Home appliances, such as washing machines, refrigerators, air conditioners and sewing machines

### Description

This intelligent power module provides a compact, high performance AC motor drive in a simple, rugged design. Combining ST proprietary control ICs with the most advanced short-circuit-rugged IGBT system technology, this device is ideal for 3-phase inverters in applications such as

**Table 1. Device summary**

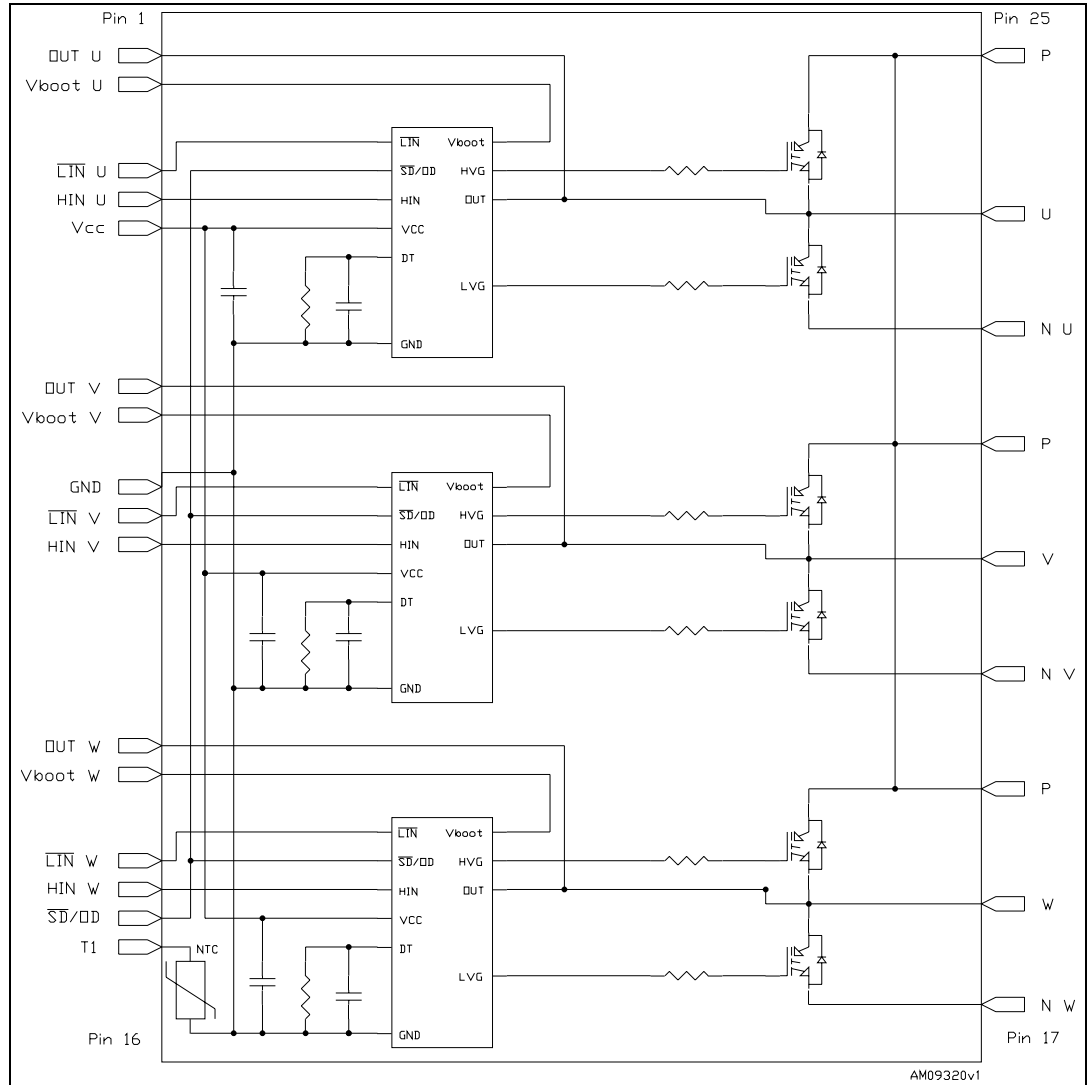
Order code	Marking	Package	Packaging
STGIPS10K60T	GIPS10K60T	SDIP-25L	Tube

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# 1 Internal block diagram and pin configuration

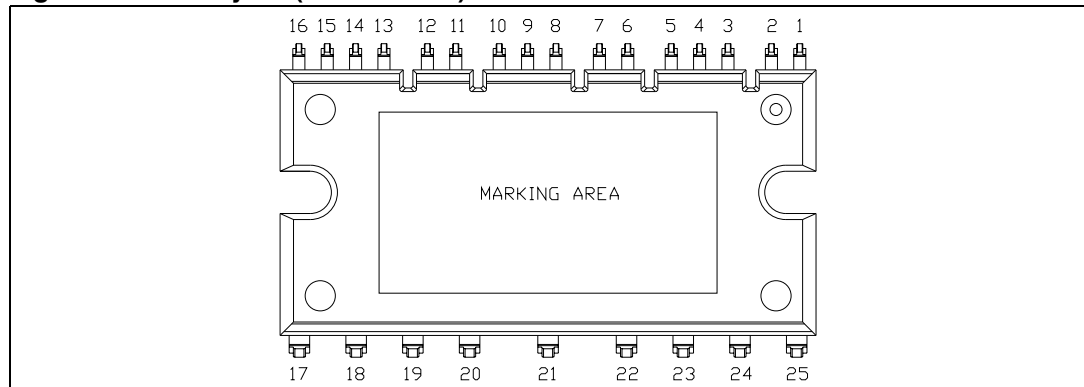
Figure 1. Internal block diagram



**Table 2. Pin description**

Pin n°	Symbol	Description
1	OUT <sub>U</sub>	High side reference output for U phase
2	V <sub>boot U</sub>	Bootstrap voltage for U phase
3	$\overline{\text{LIN}}_{\text{U}}$	Low side logic input for U phase
4	HIN <sub>U</sub>	High side logic input for U phase
5	V <sub>CC</sub>	Low voltage power supply
6	OUT <sub>V</sub>	High side reference output for V phase
7	V <sub>boot V</sub>	Bootstrap voltage for V phase
8	GND	Ground
9	$\overline{\text{LIN}}_{\text{V}}$	Low side logic input for V phase
10	HIN <sub>V</sub>	High side logic input for V phase
11	OUT <sub>W</sub>	High side reference output for W phase
12	V <sub>boot W</sub>	Bootstrap voltage for W phase
13	$\overline{\text{LIN}}_{\text{W}}$	Low side logic input for W phase
14	HIN <sub>W</sub>	High side logic input for W phase
15	$\overline{\text{SD}} / \text{OD}$	Shut down logic input (active low) / open drain (comparator output)
16	T1	NTC thermistor terminal
17	N <sub>W</sub>	Negative DC input for W phase
18	W	W phase output
19	P	Positive DC input
20	N <sub>V</sub>	Negative DC input for V phase
21	V	V phase output
22	P	Positive DC input
23	N <sub>U</sub>	Negative DC input for U phase
24	U	U phase output
25	P	Positive DC input

**Figure 2. Pin layout (bottom view)**



## 2 Electrical ratings

### 2.1 Absolute maximum ratings

**Table 3. Inverter part**

Symbol	Parameter	Value	Unit
$V_{PN}$	Supply voltage applied between P - N <sub>U</sub> , N <sub>V</sub> , N <sub>W</sub>	450	V
$V_{PN(surge)}$	Supply voltage (surge) applied between P - N <sub>U</sub> , N <sub>V</sub> , N <sub>W</sub>	500	V
$V_{CES}$	Each IGBT collector emitter voltage ( $V_{IN}^{(1)} = 0$ )	600	V
$\pm I_C^{(2)}$	Each IGBT continuous collector current at $T_C = 25^\circ\text{C}$	10	A
$\pm I_{CP}^{(3)}$	Each IGBT pulsed collector current	20	A
$P_{TOT}$	Each IGBT total dissipation at $T_C = 25^\circ\text{C}$	33	W
$t_{scw}$	Short-circuit withstand time, $V_{CE} = 0.5 V_{(BR)CES}$ $T_j = 125^\circ\text{C}$ , $V_{CC} = V_{boot} = 15\text{ V}$ , $V_{IN}^{(1)} = 5\text{ V}$	5	$\mu\text{s}$

1. Applied between HIN<sub>i</sub>,  $\overline{\text{LIN}}_i$  and GND for  $i = U, V, W$ .

2. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(max)} - T_C}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_C(T_C))}$$

3. Pulse width limited by max junction temperature.

**Table 4. Control part**

Symbol	Parameter	Min.	Max.	Unit
$V_{OUT}$	Output voltage applied between OUT <sub>U</sub> , OUT <sub>V</sub> , OUT <sub>W</sub> - GND	$V_{boot} - 21$	$V_{boot} + 0.3$	V
$V_{CC}$	Low voltage power supply	- 0.3	21	V
$V_{boot}$	Bootstrap voltage	- 0.3	620	V
$V_{IN}$	Logic input voltage applied between HIN, $\overline{\text{LIN}}$ and GND	- 0.3	15	V
$V_{SD/OD}$	Open drain voltage	- 0.3	15	V
$dV_{OUT}/dt$	Allowed output slew rate		50	V/ns

**Table 5. Total system**

Symbol	Parameter	Value	Unit
$V_{ISO}$	Isolation withstand voltage applied between each pin and heatsink plate (AC voltage, $t = 60$ sec.)	2500	V
$T_C$	Module case operation temperature	-40 to 125	°C
$T_J$	Power chips operating junction temperature	-40 to 150	°C

## 2.2 Thermal data

**Table 6. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thJC}$	Thermal resistance junction-case single IGBT max.	3.8	°C/W
	Thermal resistance junction-case single diode max.	5.5	°C/W

### 3 Electrical characteristics

$T_J = 25\text{ °C}$  unless otherwise specified.

**Table 7. Inverter part**

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{CC} = V_{boot} = 15\text{ V}$ , $V_{IN}^{(1)} = 5\text{ V}$ , $I_C = 5\text{ A}$	-	2.1	2.5	V
		$V_{CC} = V_{boot} = 15\text{ V}$ , $V_{IN}^{(1)} = 5\text{ V}$ , $I_C = 5\text{ A}$ , $T_J = 125\text{ °C}$	-	1.8		
$I_{CES}$	Collector-cut off current ( $V_{IN}^{(1)} = 0$ "logic state")	$V_{CE} = 550\text{ V}$ $V_{CC} = V_{boot} = 15\text{ V}$	-		150	$\mu\text{A}$
$V_F$	Diode forward voltage	( $V_{IN}^{(1)} = 0$ "logic state"), $I_C = 5\text{ A}$	-		1.9	V
<b>Inductive load switching time and energy</b>						
$t_{on}$	Turn-on time	$V_{DD} = 300\text{ V}$ , $V_{CC} = V_{boot} = 15\text{ V}$ , $V_{IN}^{(1)} = 0 \div 5\text{ V}$ , $I_C = 5\text{ A}$ (see <a href="#">Figure 4</a> )	-	320	-	ns
$t_{c(on)}$	Crossover time (on)		-	70	-	
$t_{off}$	Turn-off time		-	430	-	
$t_{c(off)}$	Crossover time (off)		-	135	-	
$t_{rr}$	Reverse recovery time		-	130	-	
$E_{on}$	Turn-on switching losses		-	65	-	$\mu\text{J}$
$E_{off}$	Turn-off switching losses		-	75	-	

1. Applied between  $HIN_i$ ,  $\overline{LIN}_i$  and GND for  $i = U, V, W$  (LIN inputs are active-low)..

**Note:**  $t_{ON}$  and  $t_{OFF}$  include the propagation delay time of the internal drive.  $t_{C(ON)}$  and  $t_{C(OFF)}$  are the switching time of IGBT itself under the internally given gate driving condition.

Figure 3. Switching time test circuit

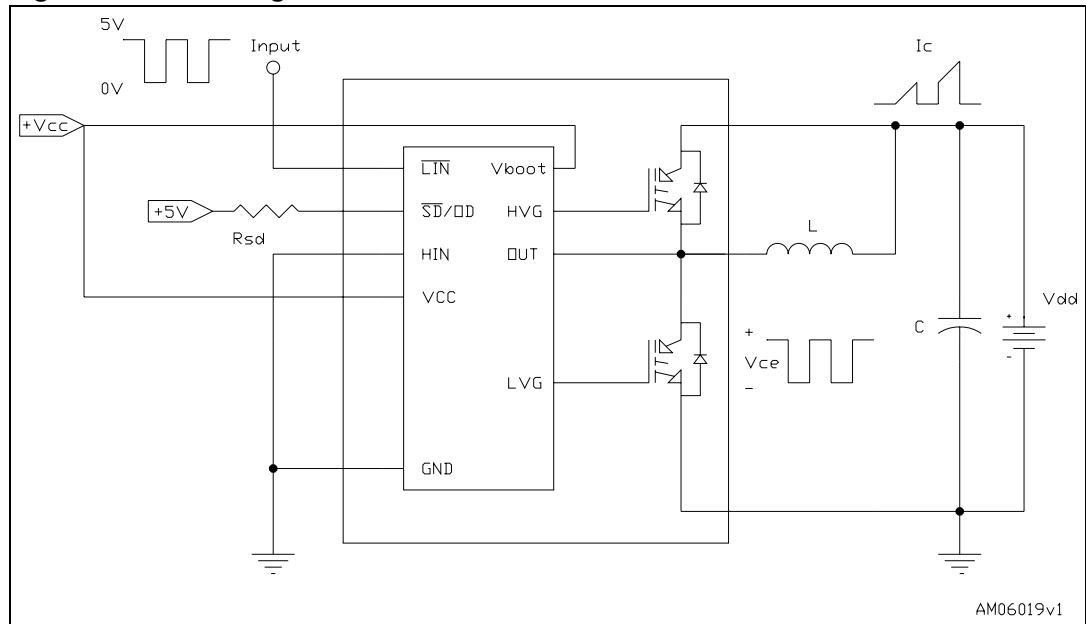
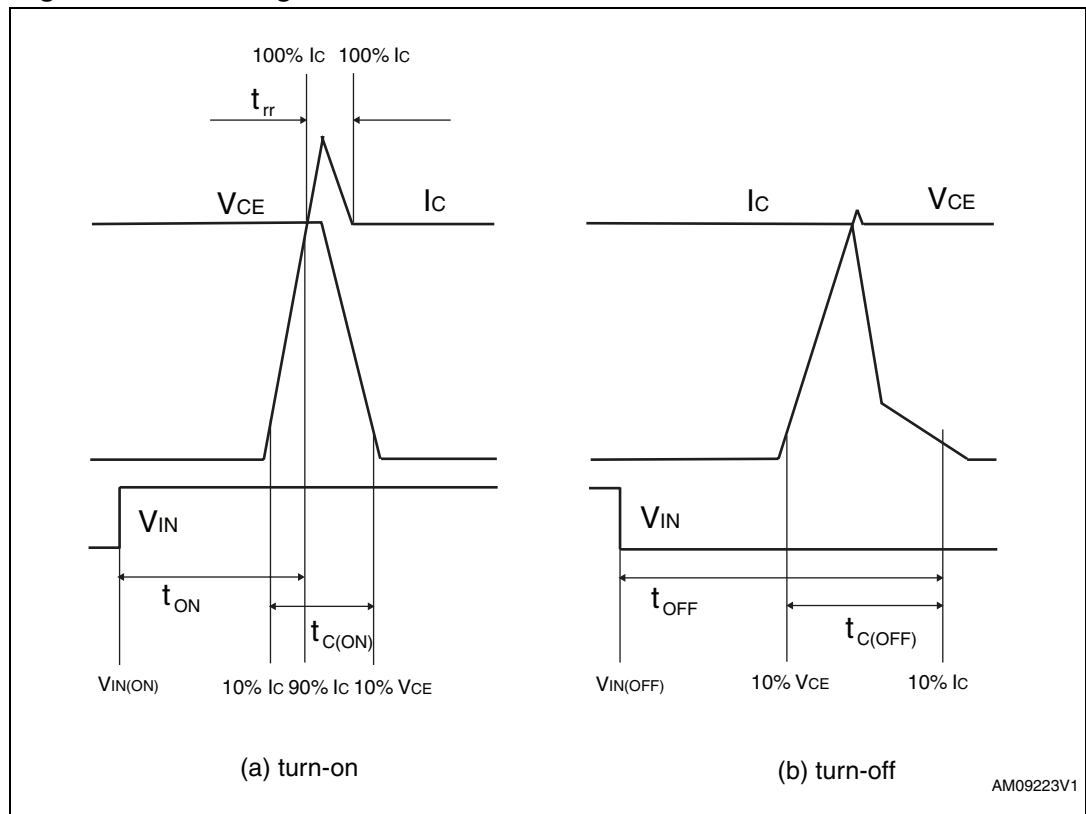


Figure 4. Switching time definition



Note: Figure 4 "Switching time definition" refers to HIN inputs (active high). For LIN inputs (active low), VIN polarity must be inverted for turn-on and turn-off.



### 3.1 Control part

**Table 8. Low voltage power supply ( $V_{CC} = 15\text{ V}$  unless otherwise specified)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{CC\_hys}$	$V_{CC}$ UV hysteresis		1.2	1.5	1.8	V
$V_{CC\_thON}$	$V_{CC}$ UV turn ON threshold		11.5	12	12.5	V
$V_{CC\_thOFF}$	$V_{CC}$ UV turn OFF threshold		10	10.5	11	V
$I_{qccu}$	Undervoltage quiescent supply current	$V_{CC} = 10\text{ V}$ $\overline{SD}/OD = 5\text{ V}$ ; $\overline{LIN} = 5\text{ V}$ ; $HIN = 0$			450	$\mu\text{A}$
$I_{qcc}$	Quiescent current	$V_{CC} = 15\text{ V}$ $\overline{SD}/OD = 5\text{ V}$ ; $\overline{LIN} = 5\text{ V}$ $HIN = 0$			3.5	mA

**Table 9. Bootstrapped voltage ( $V_{CC} = 15\text{ V}$  unless otherwise specified)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{BS\_hys}$	$V_{BS}$ UV hysteresis		1.2	1.5	1.8	V
$V_{BS\_thON}$	$V_{BS}$ UV turn ON threshold		10.6	11.5	12.4	V
$V_{BS\_thOFF}$	$V_{BS}$ UV turn OFF threshold		9.1	10	10.9	V
$I_{QBSU}$	Undervoltage $V_{BS}$ quiescent current	$V_{BS} < 9\text{ V}$ $\overline{SD}/OD = 5\text{ V}$ ; $\overline{LIN}$ and $HIN = 5\text{ V}$		70	110	$\mu\text{A}$
$I_{QBS}$	$V_{BS}$ quiescent current	$V_{BS} = 15\text{ V}$ $\overline{SD}/OD = 5\text{ V}$ ; $\overline{LIN}$ and $HIN = 5\text{ V}$		150	210	$\mu\text{A}$
$R_{DS(on)}$	Bootstrap driver on resistance	LVG ON		120		$\Omega$

**Table 10. Logic inputs ( $V_{CC} = 15\text{ V}$  unless otherwise specified)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{il}$	Low logic level voltage				0.8	V
$V_{ih}$	High logic level voltage		2.25			V
$I_{HINh}$	HIN logic "1" input bias current	$HIN = 15\text{ V}$	110	175	260	$\mu\text{A}$
$I_{HINl}$	HIN logic "0" input bias current	$HIN = 0\text{ V}$			1	$\mu\text{A}$
$I_{LINl}$	$\overline{LIN}$ logic "1" input bias current	$\overline{LIN} = 0\text{ V}$	3	6	20	$\mu\text{A}$
$I_{LINh}$	$\overline{LIN}$ logic "0" input bias current	$\overline{LIN} = 15\text{ V}$			1	$\mu\text{A}$
$I_{SDh}$	$\overline{SD}$ logic "0" input bias current	$\overline{SD} = 15\text{ V}$	30	120	300	$\mu\text{A}$
$I_{SDl}$	$\overline{SD}$ logic "1" input bias current	$\overline{SD} = 0\text{ V}$			3	$\mu\text{A}$
Dt	Dead time	see <a href="#">Figure 8</a>		600		ns

**Table 11. Shut down characteristics ( $V_{CC} = 15\text{ V}$  unless otherwise specified)**

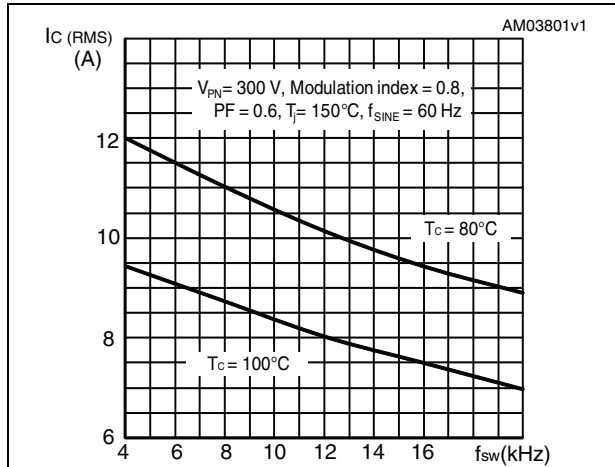
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{sd}$	Shut down to high / low side driver propagation delay	$V_{OUT} = 0, V_{boot} = V_{CC}, V_{IN} = 0$ to 3.3 V	50	125	200	ns

**Table 12. Truth table**

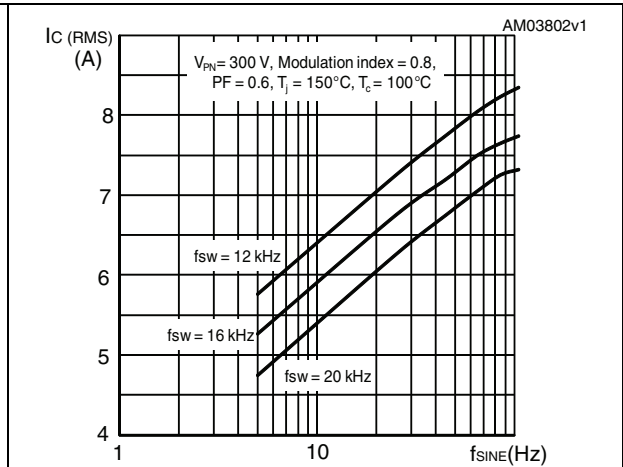
Condition	Logic input ( $V_I$ )			Output	
	$\overline{SD/OD}$	$\overline{LIN}$	HIN	LVG	HVG
Shutdown enable half-bridge tri-state	L	X	X	L	L
Interlocking half-bridge tri-state	H	L	H	L	L
0 "logic state" half-bridge tri-state	H	H	L	L	L
1 "logic state" low side direct driving	H	L	L	H	L
1 "logic state" high side direct driving	H	H	H	L	H

Note: X: don't care

**Figure 5. Maximum  $I_{C(RMS)}$  current vs. switching frequency (1)**



**Figure 6. Maximum  $I_{C(RMS)}$  current vs.  $f_{SINE}$  (1)**



1. Simulated curves refer to typical IGBT parameters and maximum  $R_{thJC}$ .

### 3.1.1 NTC thermistor

**Table 13. NTC thermistor**

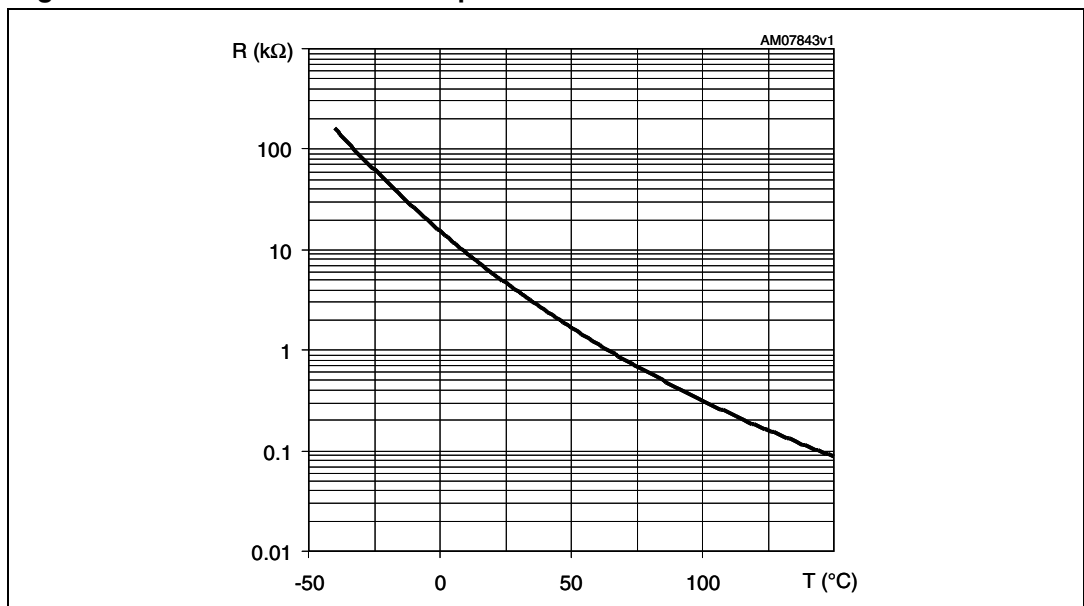
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit.
R <sub>25</sub>	Resistance	T <sub>C</sub> = 25°C		4.7		kΩ
R <sub>125</sub>	Resistance	T <sub>C</sub> = 125°C		160		Ω
B	B-constant	T <sub>C</sub> = 25°C		3950		K
T	Operating temperature		-40		150	°C

**Equation 1: resistance variation vs. temperature**

$$R(T) = R_{25} \cdot e^{B \left( \frac{1}{T} - \frac{1}{298} \right)}$$

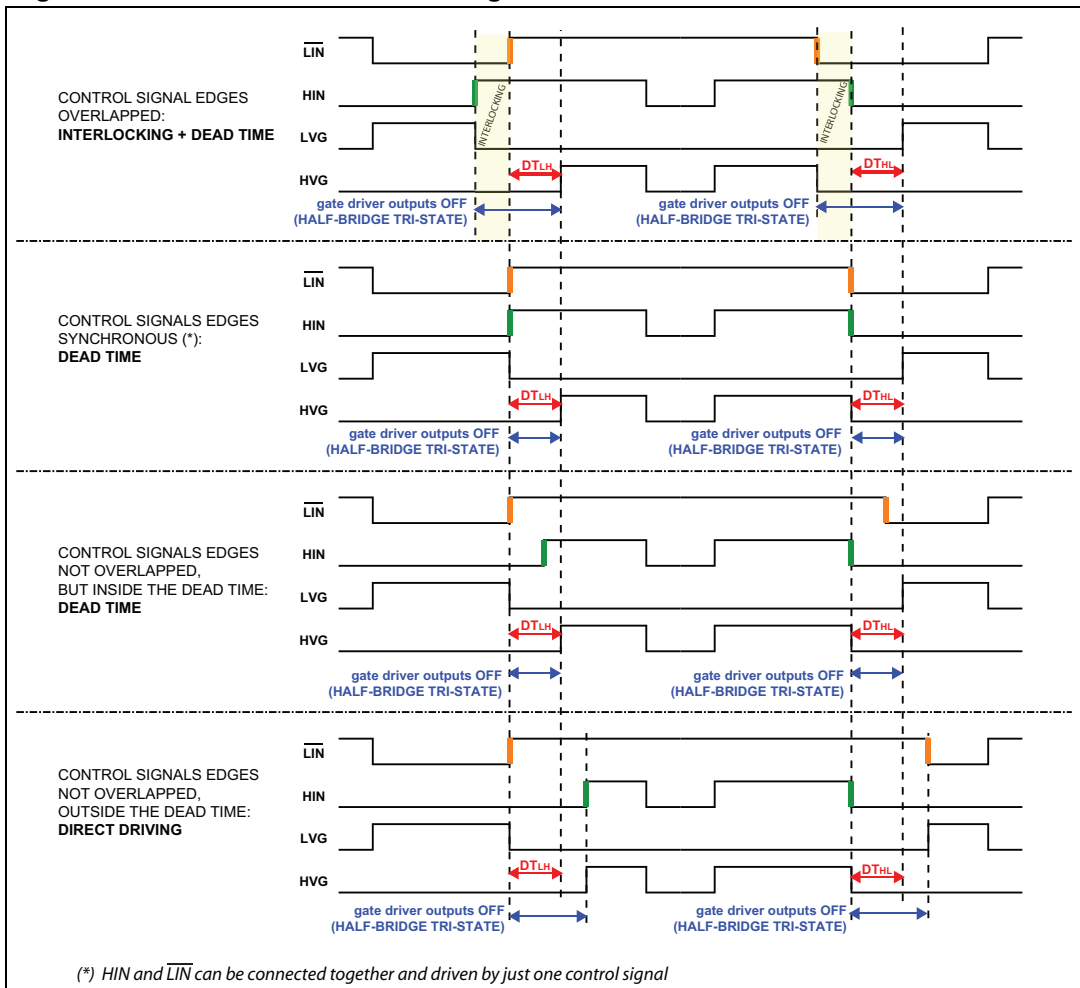
Where T are temperatures in Kelvins

**Figure 7. NTC resistance vs. temperature**



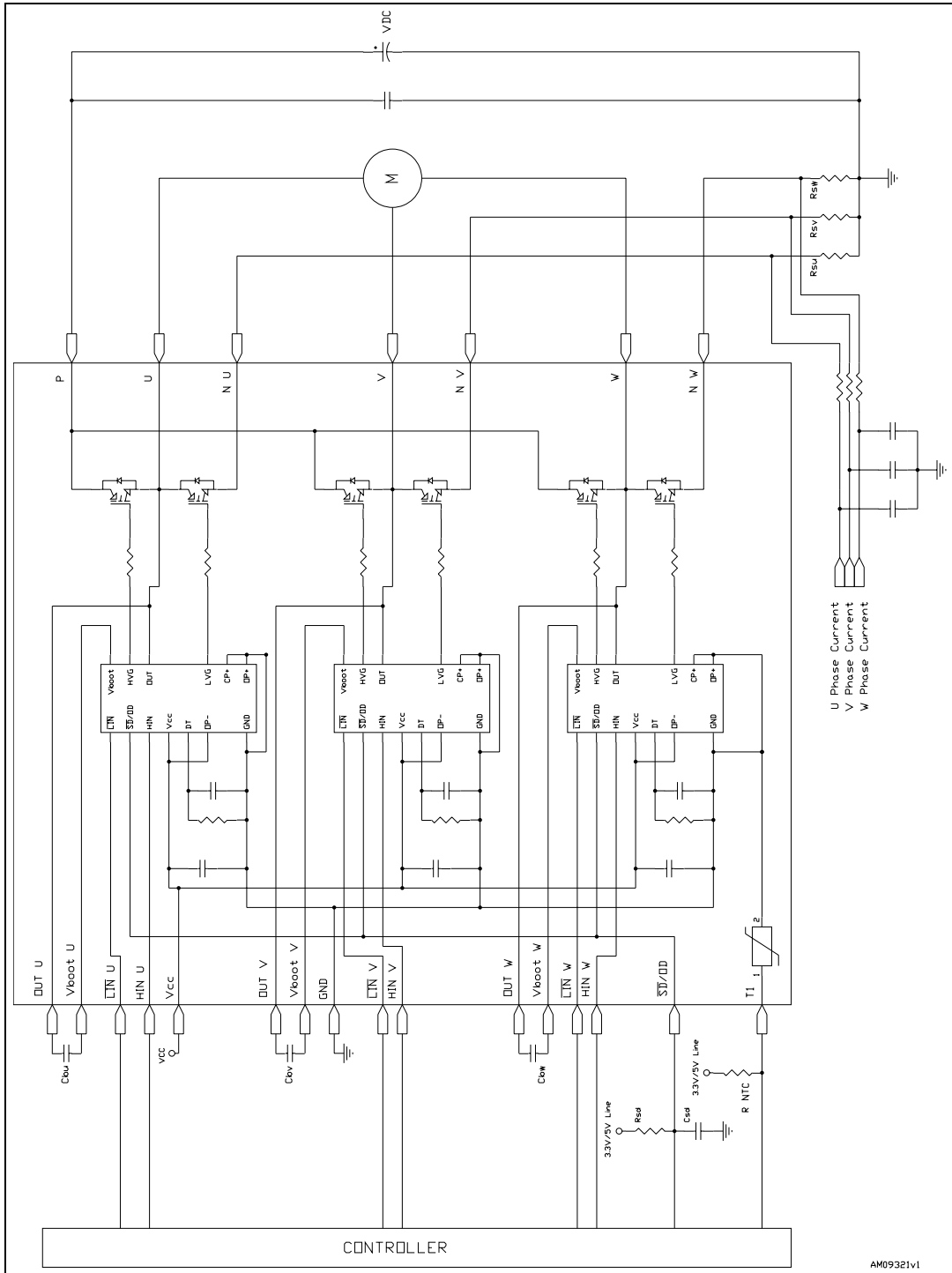
### 3.2 Waveforms definitions

Figure 8. Dead time and interlocking waveforms definitions



# 4 Applications information

Figure 9. Typical application circuit



### 4.1 Recommendations

- Input signal HIN is active high logic. A 85 kΩ (typ.) pull down resistor is built-in for each high side input. If an external RC filter is used, for noise immunity, pay attention to the variation of the input signal level.
- Input signal /LIN is active low logic. A 720 kΩ (typ.) pull-up resistor, connected to an internal 5 V regulator through a diode, is built-in for each low side input.
- To prevent the input signals oscillation, the wiring of each input should be as short as possible.
- By integrating an application specific type HVIC inside the module, direct coupling to MCU terminals without any opto-coupler is possible.
- Each capacitor should be located as nearby the pins of IPM as possible.
- Low inductance shunt resistors should be used for phase leg current sensing.
- Electrolytic bus capacitors should be mounted as close to the module bus terminals as possible. Additional high frequency ceramic capacitor mounted close to the module pins will further improve performance.
- The  $\overline{SD}/OD$  signal should be pulled up to 5 V / 3.3 V with an external resistor.

**Table 14. Recommended operating conditions**

Symbol	Parameter	Conditions	Value			Unit
			Min.	Typ.	Max.	
V <sub>PN</sub>	Supply voltage	Applied between P-Nu, Nv, Nw		300	400	V
V <sub>CC</sub>	Control supply voltage	Applied between V <sub>CC</sub> -GND	13.5	15	18	V
V <sub>BS</sub>	High side bias voltage	Applied between V <sub>BOOT1</sub> -OUT <sub>i</sub> for i = U, V, W	13		18	V
t <sub>dead</sub>	Blanking time to prevent arm-short	For each input signal	1			μs
f <sub>PWM</sub>	Pwm input signal	-40°C < T <sub>c</sub> < 100°C -40°C < T <sub>j</sub> < 125°C			20	kHz
T <sub>C</sub>	Case operation temperature				100	°C

For further details refer to AN3338.

## 5 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

Please refer to dedicated technical note TN0107 for mounting instructions.

**Table 15. SDIP-25L mechanical data**

Dim.	mm.		
	Min.	Typ.	Max.
A	43.90	44.40	44.90
A1	1.15	1.35	1.55
A2	1.40	1.60	1.80
A3	38.90	39.40	39.90
B	21.50	22.00	22.50
B1	11.25	11.85	12.45
B2	24.83	25.23	25.63
C	5.00	5.40	6.00
C1	6.50	7.00	7.50
C2	11.20	11.70	12.20
e	2.15	2.35	2.55
e1	3.40	3.60	3.80
e2	4.50	4.70	4.90
e3	6.30	6.50	6.70
D		33.30	
D1		5.55	
E		11.20	
E1		1.40	
F	0.85	1.00	1.15
F1	0.35	0.50	0.65
R	1.55	1.75	1.95
T	0.45	0.55	0.65
V	0°		6°

Figure 10. SDIP-25L drawing dimensions data

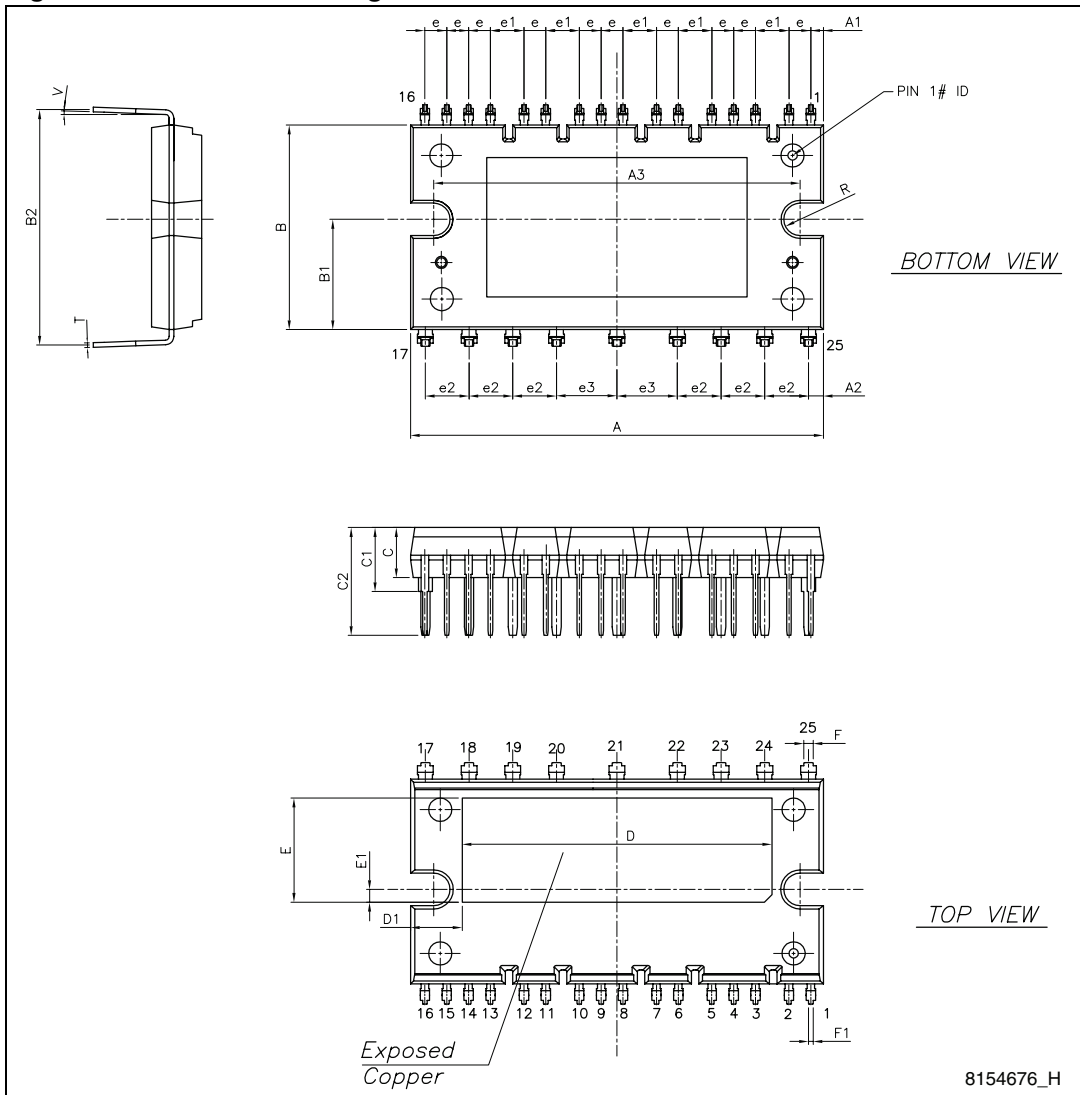




Figure 11. Packaging specifications of SDIP-25L package

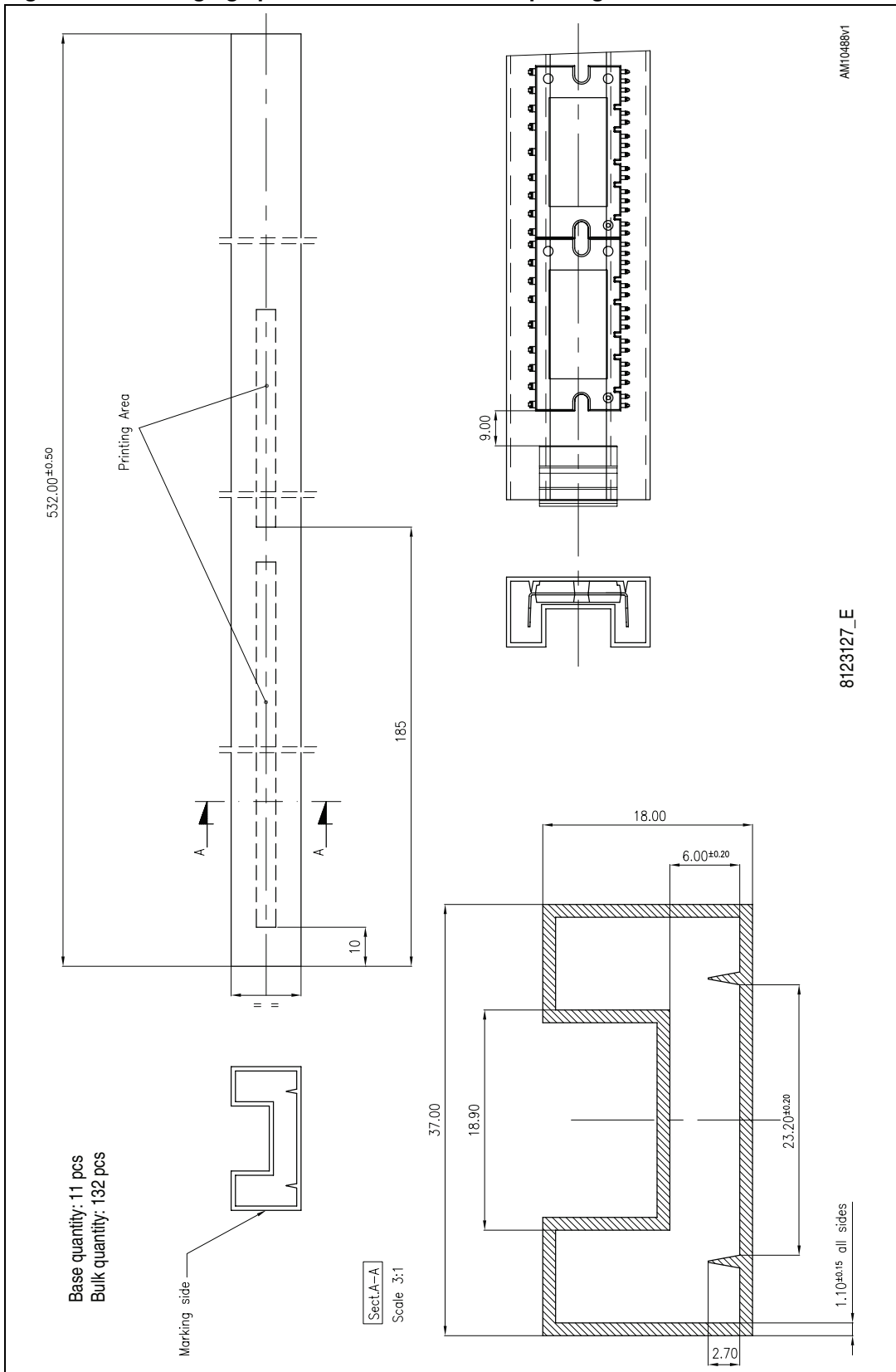
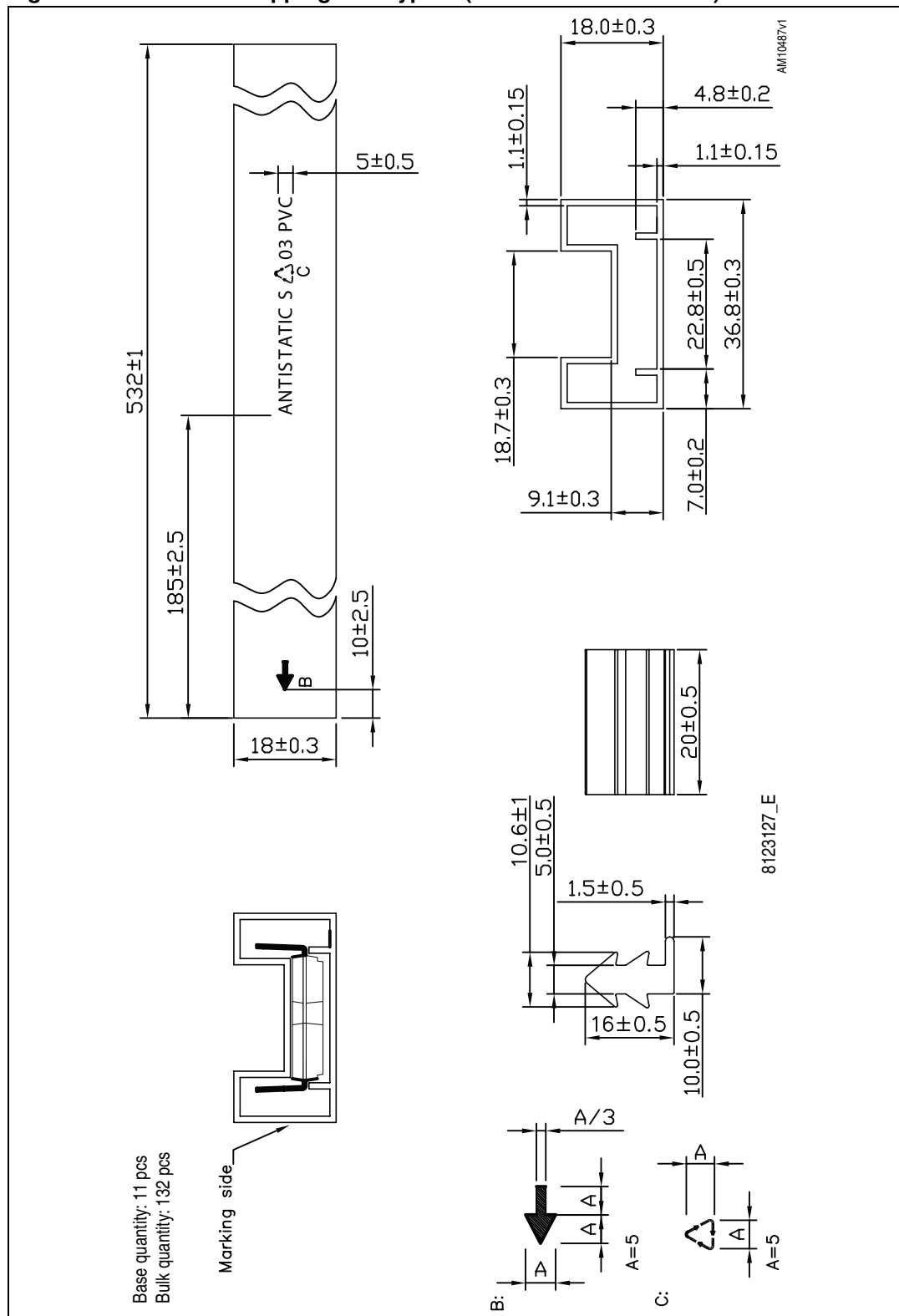


Figure 12. SDIP-25L shipping tube type B (dimensions are in mm.)



## 6 Revision history

**Table 16. Document revision history**

Date	Revision	Changes
07-Mar-2011	1	Initial release.
14-Sep-2011	2	Modified <a href="#">Section 3.1.1 on page 11</a> .
28-Aug-2012	3	Modified: Min. and Max. value <a href="#">Table 4 on page 5</a> . Updated: <a href="#">Table 15 on page 15</a> , <a href="#">Figure 10 on page 16</a> and <a href="#">Figure 11 on page 17</a> . Added: <a href="#">Figure 12 on page 18</a> .

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